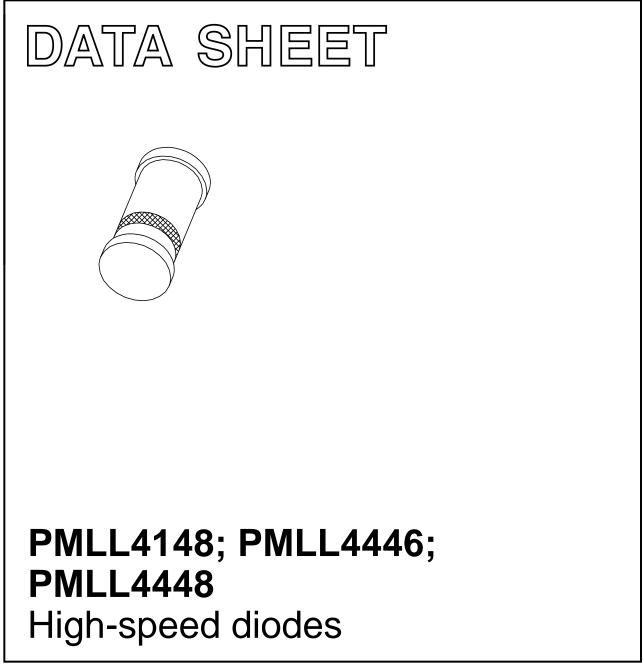
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of April 1996 File under Discrete Semiconductors, SC01 1996 Sep 18



PMLL4148; PMLL4446; PMLL4448

FEATURES

- Small hermetically sealed glass SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- High-speed switching
- Fast logic applications.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

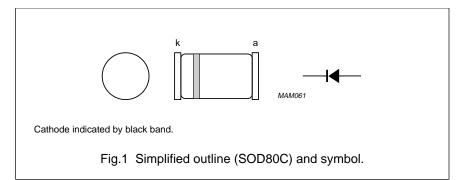
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		_	75	V
V _R	continuous reverse voltage		_	75	V
I _F	continuous forward current	see Fig.2; note 1	_	200	mA
I _{FRM}	repetitive peak forward current		_	450	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	А
		t = 1 ms	_	1	А
		t = 1 s	_	0.5	A
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	500	mW
T _{stg}	storage temperature		-65	+200	°C
Tj	junction temperature		_	200	°C

Note

1. Device mounted on an FR4 printed-circuit board.



The PMLL4148, PMLL4446, PMLL4448 are high-speed switching diodes fabricated in planar technology, and encapsulated in small hermetically sealed glass SOD80C SMD packages.



PMLL4148; PMLL4446; PMLL4448

ELECTRICAL CHARACTERISTICS

 $T_i = 25 \ ^{\circ}C$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _F	forward voltage	see Fig.3			
	PMLL4148	I _F = 10 mA	_	1.0	V
	PMLL4446	I _F = 20 mA	_	1.0	V
	PMLL4448	I _F = 5 mA	620	720	mV
		I _F = 100 mA	_	1.0	V
I _R	reverse current	V _R = 20 V; see Fig.5		25	nA
		V_R = 20 V; T_j = 150 °C; see Fig.5	_	50	μA
I _R	reverse current; PMLL4448	V_R = 20 V; T _j = 100 °C; see Fig.5	_	3	μA
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 0; \text{ see Fig.6}$		4	pF
t _{rr}	reverse recovery time	when switched from $I_F = 10$ mA to $I_R = 60$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA; see Fig.7		4	ns
V _{fr}	forward recovery voltage	when switched from $I_F = 50$ mA; $t_r = 20$ ns; see Fig.8	—	2.5	V

THERMAL CHARACTERISTICS

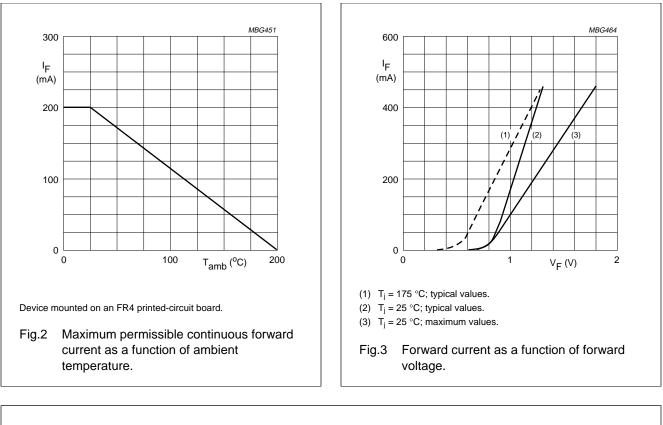
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		300	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	350	K/W

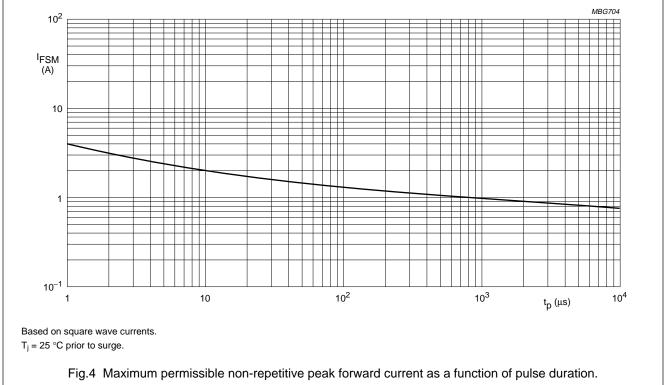
Note

1. Device mounted on an FR4 printed-circuit board.

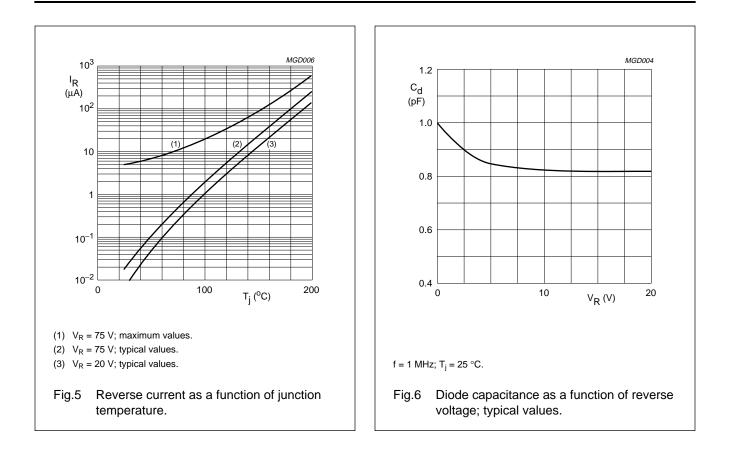
PMLL4148; PMLL4446; PMLL4448



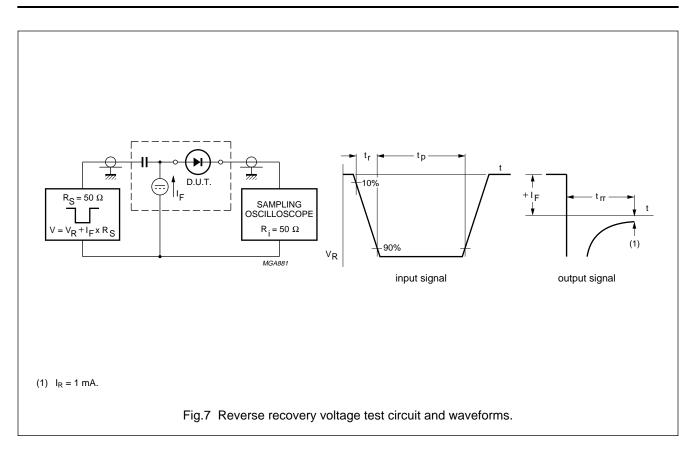


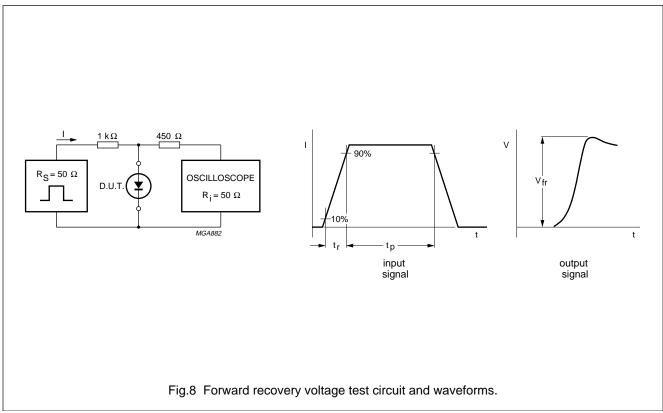


PMLL4148; PMLL4446; PMLL4448



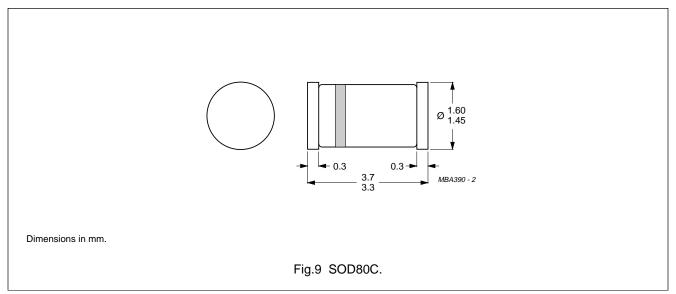
PMLL4148; PMLL4446; PMLL4448





PMLL4148; PMLL4446; PMLL4448

PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		
more of the limiting values m of the device at these or at a	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or hay cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification miting values for extended periods may affect device reliability.	
Application information		

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.